

MOS Fied Effect Transistor

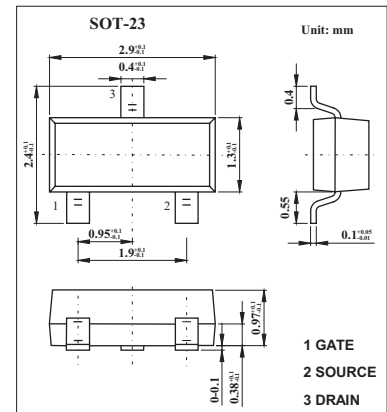
2SJ207

■ Features

- Directly driven by lcs having a 3V poer supply.
- Has low on-state resistance

$R_{DS(on)}=4\ \Omega$ MAX.@ $V_{GS}=-2.5V$, $I_D=-30mA$

$R_{DS(on)}=1.5\ \Omega$ MAX.@ $V_{GS}=-4.0V$, $I_D=-500mA$



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain to source voltage $V_{GS}=0$	V_{DS}	-16	V
Gate to source voltage $V_{DS}=0$	V_{GS}	± 16	V
Drain current (DC)	I_D	± 1.0	A
Drain current(pulse) *	I_D	± 2.0	A
Power dissipation	P_D	2.0	W
Channel temperature	T_{ch}	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

* $PW \leq 10\ ms$; $d \leq 50\%$.

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Drain cut-off current	I_{DSS}	$V_{DS}=-16V, V_{GS}=0$			-10	μA
Gate leakage current	I_{GSS}	$V_{GS}=\pm 16V, V_{DS}=0$			± 5	μA
Gate cut-off voltage	$V_{GS(off)}$	$V_{DS}=-5.0V, I_D=-1mA$	-1.4	-1.9	-2.4	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS}=-3.0V, I_D=-500mA$	0.4	0.7		s
Drain to source on-state resistance	$R_{DS(on)}$	$V_{GS}=-2.5V, I_D=-30mA$		2.6	4.0	Ω
		$V_{GS}=-4V, I_D=-500mA$		0.9	1.5	Ω
Input capacitance	C_{iss}	$V_{DS}=-3.0V, V_{GS}=0, f=1MHz$		180		pF
Output capacitance	C_{oss}			160		pF
Reverse transfer capacitance	C_{rss}			50		pF
Turn-on delay time	$t_{d(on)}$	$V_{GS(on)}=-3V, R_G=10\ \Omega, V_{DD}=-3V, I_D=-100mA, R_L=30\ \Omega$		180		ns
Rise time	t_r			500		ns
Turn-off delay time	$t_{d(off)}$			130		ns
Fall time	t_f			240		ns

■ Marking

Marking	PE
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